

Fabio Pezzoli

List of Publications by Year in descending order

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39
times ranked

882
citing authors

#	ARTICLE	IF	CITATIONS
1	Conductive n-type gallium nitride thin films prepared by sputter deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 042703.	2.1	0
2	Optical Spin Orientation in Ge-Based Heterostructures. Topics in Applied Physics, 2021, , 237-282.	0.8	0
3	Magneto-optical investigation of the dynamics of spin-polarized carriers in GeSn heterostructures. , 2021, , .		0
4	Single-Tear Proteomics: A Feasible Approach to Precision Medicine. International Journal of Molecular Sciences, 2021, 22, 10750.	4.1	25
5	Tear-Based Vibrational Spectroscopy Applied to Amyotrophic Lateral Sclerosis. Analytical Chemistry, 2021, 93, 16995-17002.	6.5	16
6	Photonic Band Gap and Light Routing in Self-Assembled Lattices of Epitaxial $\text{Ge}_{1-x}\text{Si}_x$ Microstructures. Physical Review Applied, 2021, 16, .	3.8	1
7	Broadband control of the optical properties of semiconductors through site-controlled self-assembly of microcrystals. Optics Express, 2020, 28, 24981.	3.4	6
8	Continuous-Wave Magneto-Optical Determination of the Carrier Lifetime in Coherent $\text{Ge}_{1-x}\text{Si}_x$ Heterostructures. Physical Review Applied, 2020, 14, .	3.8	7
9	Ambient atmosphere laser-induced local ripening of MoS_2 nanoparticles. Journal of Materials Chemistry C, 2019, 7, 13261-13266.	5.5	2
10	Critical strain for Sn incorporation into spontaneously graded Ge/GeSn core/shell nanowires. Nanoscale, 2018, 10, 7250-7256.	5.6	28
11	Optically reconfigurable polarized emission in Germanium. Scientific Reports, 2018, 8, 11119.	3.3	9
12	Exceptional thermal strain reduction by a tilting pillar architecture: Suspended Ge layers on Si (001). Materials and Design, 2017, 116, 144-151.	7.0	9
13	Strain Engineering in Highly Mismatched SiGe/Si Heterostructures. Materials Science in Semiconductor Processing, 2017, 70, 117-122.	4.0	8
14	Progress towards Spin-Based Light Emission in Group IV Semiconductors. Electronics (Switzerland), 2017, 6, 19.	3.1	14
15	Highly Mismatched, Dislocation-Free SiGe/Si Heterostructures. Advanced Materials, 2016, 28, 884-888.	21.0	37
16	Disentangling nonradiative recombination processes in Ge micro-crystals on Si substrates. Applied Physics Letters, 2016, 108, .	3.3	14
17	Strong confinement-induced engineering of the g factor and lifetime of conduction electron spins in Ge quantum wells. Nature Communications, 2016, 7, 13886.	12.8	28
18	Towards a uniform and large-scale deposition of MoS_2 nanosheets via sulfurization of ultra-thin Mo-based solid films. Nanotechnology, 2016, 27, 175703.	2.6	59

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19	Temperature-Dependent Photoluminescence Characteristics of GeSn Epitaxial Layers. ACS Photonics, 2016, 3, 2004-2009.	6.6	43
20	Elastic and Plastic Stress Relaxation in Highly Mismatched SiGe/Si Crystals. MRS Advances, 2016, 1, 3403-3408.	0.9	1
21	Optical orientation of electron spins and valence-band spectroscopy in germanium. Physical Review B, 2015, 91, .	3.2	11
22	Local uniaxial tensile strain in germanium of up to 4% induced by SiGe epitaxial nanostructures. Applied Physics Letters, 2015, 107, .	3.3	18
23	Structural investigations of the $\text{12Si}^{\text{6}}\text{Ge}$ superstructure. Journal of Applied Crystallography, 2015, 48, 262-268.	4.5	3
24	Emission Engineering in Germanium Nanoresonators. ACS Photonics, 2015, 2, 53-59.	6.6	27
25	Valley-dependent spin polarization and long-lived electron spins in germanium. Applied Physics Letters, 2014, 105, 152404.	3.3	26
26	Ge Crystals on Si Show Their Light. Physical Review Applied, 2014, 1, .	3.8	34
27	3D heteroepitaxy of mismatched semiconductors on silicon. Thin Solid Films, 2014, 557, 42-49.	1.8	18
28	Spin-resolved study of direct band-gap recombination in bulk Ge. Proceedings of SPIE, 2014, , .	0.8	0
29	Spin and energy relaxation in germanium studied by spin-polarized direct-gap photoluminescence. Physical Review B, 2013, 88, .	3.2	32
30	Tailoring the spin polarization in Ge/SiGe multiple quantum wells. , 2013, , .		2
31	Optical tailoring of carrier spin polarization in Ge/SiGe multiple quantum wells. Applied Physics Letters, 2013, 102, 012408.	3.3	14
32	Holes in germanium quantum wells: spin relaxation and temperature dynamics. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1238-1241.	0.8	0
33	Optical Spin Injection and Spin Lifetime in Ge Heterostructures. Physical Review Letters, 2012, 108, 156603.	7.8	89
34	Optical spin injection and spin lifetime in Ge heterostructures. , 2012, , .		0
35	Composition profiling of inhomogeneous SiGe nanostructures by Raman spectroscopy. Nanoscale Research Letters, 2012, 7, 633.	5.7	6
36	Optical spin injection in SiGe heterostructures. Proceedings of SPIE, 2011, , .	0.8	2

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37	Raman spectroscopy of Si _{1-x} Ge _x epilayers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 127-131.	3.5	45
38	Optical Manipulation of the Rashba Effect in Germanium Quantum Wells. Advanced Optical Materials, 0, , 2201082.	7.3	1